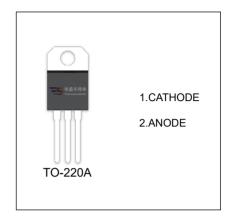


MBR1030,35,40,45,50

SCHOTTKY BARRIER RECTIFIER

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



MAXIMUM RATINGS (T_a =25°C unless otherwise noted)

Symbol	Parameter	Value					
		MBR1030	MBR1035	MBR1040	MBR1045	MBR1050	Unit
V _{RRM}	Peak repetitive reverse voltage						
V _{RWM}	Working peak reverse voltage	30	35	40	45	50	V
V _R	DC blocking voltage						
V _{R(RMS)}	RMS reverse voltage	21	24.5	28	31.5	35	V
lo	Average rectified output current	10					Α
	Non-Repetitive peak forward surge						
I _{FSM}	current	150					
	8.3ms half sine wave						
P _D	Power dissipation	2				W	
R _{OJA}	Thermal resistance from junction to	50					°C/W
	ambient						
Tj	Operating Junction Temperature Range	-40 ~ +125					℃
T _{stg}	Storage Temperature Range	-55 ~ +150					°C



Parameter	Symbol	Device	Test conditions	Min	Тур	Max	Unit
	V _(BR)	MBR1030		30			V
		MBR1035	I _R =1mA	35			
Reverse voltage		MBR1040		40			
		MBR1045		45			
		MBR1050		50			
	I _R	MBR1030	V _R =30V			0.1	mA
		MBR1035	V _R =35V				
Reverse current		MBR1040	V _R =40V				
		MBR1045	V _R =45V				
		MBR1050	V _R =50V				
Forward voltage	V _F	MBR1030-45	I _F =10A			0.84	V
	V F	MBR1050	11-10A			0.95	
Typical junction capacitance	C _j	MBR1030-50	V _R =4V,f=1MHz		400		pF